

AurÃ©lien Olivier

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/4744371/publications.pdf>

Version: 2024-02-01

13
papers

3,524
citations

1477746

6
h-index

1372195

10
g-index

13
all docs

13
docs citations

13
times ranked

7795
citing authors

#	ARTICLE	IF	CITATIONS
1	From Bulk to Monolayer MoS ₂ : Evolution of Raman Scattering. Advanced Functional Materials, 2012, 22, 1385-1390.	7.8	3,354
2	Single-shot all-optical switching of magnetization in Tb/Co multilayer-based electrodes. Scientific Reports, 2020, 10, 5211.	1.6	68
3	Integration of Tb/Co multilayers within optically switchable perpendicular magnetic tunnel junctions. AIP Advances, 2019, 9, .	0.6	36
4	Sb-HEMT: Toward 100-mV Cryogenic Electronics. IEEE Transactions on Electron Devices, 2010, 57, 1903-1909.	1.6	18
5	Temperature-dependent spontaneous emission of PbS quantum dots inside photonic nanostructures at telecommunication wavelength. Optics Communications, 2017, 383, 555-560.	1.0	14
6	Free-standing GaAs nanowires growth on ITO glass by MOCVD. Materials Research Express, 2015, 2, 045002.	0.8	10
7	DC characteristics of InAs/AlSb HEMTs at cryogenic temperatures. , 2009, , .		6
8	Germanium-catalyzed growth of single-crystal GaN nanowires. Journal of Crystal Growth, 2016, 439, 28-32.	0.7	6
9	Gallium nitride nanowires grown by low pressure chemical vapour deposition on silicon substrate. International Journal of Nanotechnology, 2014, 11, 243.	0.1	5
10	AlSb/InAs HEMTs on InP substrate using wet and dry etching for mesa isolation. , 2008, , .		3
11	Indium Tin Oxide optical access for magnetic tunnel junctions in hybrid spintronicâ€“photonic circuits. Nanotechnology, 2020, 31, 425302.	1.3	3
12	Parameters study on the growth of GaAs nanowires on indium tin oxide by metal-organic chemical vapor deposition. Journal of Applied Physics, 2016, 119, 094305.	1.1	1
13	100mV noise performances of Te-doped Sb-HEMT. , 2010, , .		0